

SOT-89 Plastic-Encapsulated Transistors

2SB1308 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.5 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM}: -3 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -30 \text{ V}$$

Operating and storage junction temperature range

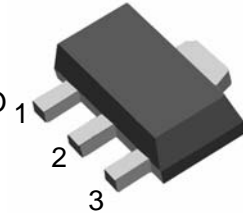
$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu\text{A}, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu\text{A}, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$		-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$		-0.5	μA
DC current gain	h_{FE}^*	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$	82	390	
Collector-emitter saturation voltage	V_{CEsat}^*	$I_C = -1.5\text{A}, I_B = -0.15\text{A}$		-0.45	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -50\text{mA}$ $f = 30\text{MHz}$	50		MHz

* Measured using pulse current.

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390

Marking	BFP,BFQ,BFR
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